8-Bit Addressable Latch

The MC74AC259/74ACT259 is a high–speed 8-bit addressable latch designed for general purpose storage applications in digital systems. It is a multifunctional device capable of storing single line data in eight addressable latches, and also a 1-of-8 decoder and demultiplexer with active HIGH outputs. The device also incorporates an active LOW Common Clear for resetting all latches, as well as an active LOW Enable. It is functionally identical to the ALS259 8-bit addressable latch.

- Serial-to-Parallel Conversion
- Eight Bits of Storage with Output of Each Bit Available
- Random (Addressable) Data Entry
- Active High Demultiplexing or Decoding Capability
- Easily Expandable
- Common Clear
- These are Pb-Free Devices

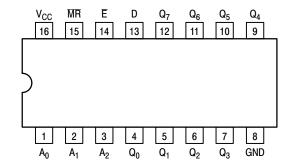


Figure 1. Pinout: 16-Lead Packages Conductors (Top View)

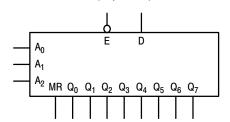


Figure 2. Logic Symbol

MODE SELECT TABLE

Ē	MR	Mode
L	Н	Addressable Latch
Н	Н	Memory
L	L	Active HIGH 8-Channel Demultiplexer
Н	L	Clear

H = HIGH Voltage Level L = LOW Voltage Level



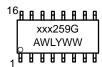
ON Semiconductor®

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MARKING DIAGRAM



SOIC-16 D SUFFIX CASE 751B



xxx = AC or ACT

A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

MODE SELECT-FUNCTION TABLE

Operating			Inp	uts						Out	puts			
Mode	MR	Ē	D	A ₀	A ₁	A ₂	Q_0	Q ₁	Q_2	Q_3	Q_4	Q_5	Q_6	Q ₇
Master Reset	L	Н	Χ	Χ	Χ	Χ	L	L	L	L	L	L	L	L
	L	L	d	L	L	L	Q = d	L	L	L	L	L	L	L
	L	L	d	Н	L	L	L	Q = d	L	L	L	L	L	L
Demultiplex	L	L	d	L	Н	L	L	L	Q = d	L	L	L	L	L
(Active HIGH Decoder when	•	•	•	•	•	•	•	•	•	•	•	•	•	•
D = H)	•	•	•	•	•	•	•	•	•	•	•	•	•	•
<i>D</i> – 11)	•	•	•	•	•	•	•	•	•	•	•	•	•	•
	L	L	d	Н	Н	Н	L	L	L	L	L	L	L	Q = d
Store (Do Nothing)	Н	Н	Х	Х	Х	Х	q ₀	q ₁	q_2	q_3	q ₄	q 5	q ₆	q ₇
	Н	L	d	L	L	L	Q = d	q ₁	q_2	q_3	q ₄	q_5	q ₆	q ₇
	Н	L	d	Н	L	L	q_0	Q = d	q_2	q_3	q_4	q_5	q_6	q ₇
A ddragachla	Н	L	d	L	Н	L	q_0	q 1	Q = d	q_3	q_4	q 5	q_6	q ₇
Addressable Latch	•	•	•	•	•	•	•	•	•	•	•	•	•	•
Laton	•	•	•	•	•	•	•	•	•	•	•	•	•	•
	•	•	•	•	•	•	•	•	•	•	•	•	•	•
	Н	L	d	Н	Н	Н	q_0	q_1	q_2	q_3	q_4	q_5	q_6	Q = d

H = HIGH Voltage Level

FUNCTIONAL DESCRIPTION

The MC74AC259/74ACT259 has four modes of operation as shown in the Mode Selection Table. In the addressable latch mode, data on the Data line (D) is written into the addressed latch. The addressed latch will follow the data input with all non–addressed latches remaining in their previous states in the memory mode. All latches remain in their previous state and are unaffected by the Data or Address inputs.

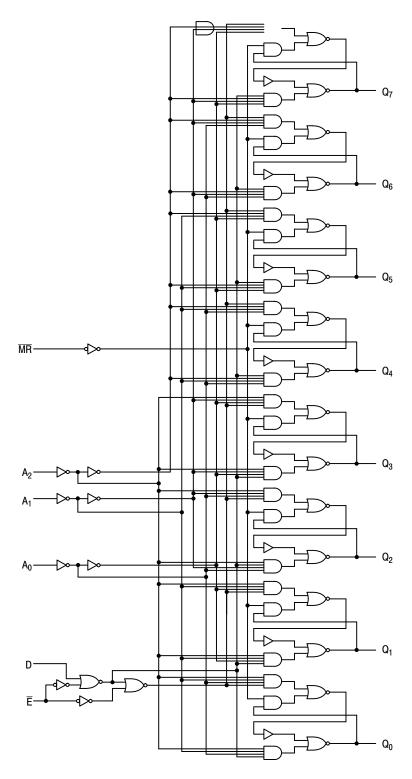
In the one–of–eight decoding or demultiplexing mode, the addressed output will follow the state of the D input with all other outputs in the LOW state. In the clear mode all outputs are LOW and unaffected by the address and data inputs. When operating the MC74AC/ACT259 as an addressable latch, changing more than one bit of the address could impose a transient wrong address. Therefore, this should only be done while in the memory mode. The Mode Select Function Table summarizes the operations of the MC74AC/ACT259.

L = LOW Voltage Level

X = Immaterial

d = HIGH or LOW Data one setup time prior to the LOW-to-HIGH Enable transition

q = Lower case letters indicate the state of the referenced output established during the last cycle in which it was addressed or cleared.



NOTE: This diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Figure 3. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	$-0.5 \le V_{CC} + 0.5$	V
Vo	DC Output Voltage (Note 1)	$-0.5 \le V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current	±20	mA
I _{OK}	DC Output Diode Current	±50	mA
I _O	DC Output Sink/Source Current	±50	mA
I _{CC}	DC Supply Current per Output Pin	±50	mA
I _{GND}	DC Ground Current per Output Pin	±50	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
TL	Lead temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction temperature under Bias	+150	°C
θ_{JA}	Thermal Resistance (Note 2)	69.1	°C/W
P _D	Power Dissipation in Still Air at 65°C (Note 3)	500	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 30% – 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 4) Machine Model (Note 5) Charged Device Model (Note 6)	> 2000 > 200 > 1000	V
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GND at 85°C (Note 7)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. I_O absolute maximum rating must be observed.
- The package thermal impedance is calculated in accordance with JESD51-7.
- 3. 500 mW at 65°C; derate to 300 mW by 10 mW/ from 65°C to 85°C.
- 4. Tested to EIA/JESD22-A114-A.
- 5. Tested to EIA/JESD22-A115-A.
- Tested to JESD22-C101-A.
- 7. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit
V	Complex Voltage	′AC	2.0	5.0	6.0	V
V _{CC}	Supply Voltage	'ACT	4.5	5.0	5.5	V
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage (Ref. to GND)	0	-	V _{CC}	V	
		V _{CC} @ 3.0 V	-	150	-	
t _r , t _f	Input Rise and Fall Time (Note 1) 'AC Devices except Schmitt Inputs	V _{CC} @ 4.5 V	-	40	_	ns/V
	7.6 Boxisso oxespt commit inputs	V _{CC} @ 5.5 V	-	25	_	
	Input Rise and Fall Time (Note 2)	V _{CC} @ 4.5 V	-	10	_	no/\/
t _r , t _f	'ACT Devices except Schmitt Inputs	V _{CC} @ 5.5 V	-	8.0	_	ns/V
T _A	Operating Ambient Temperature Range			25	85	°C
I _{OH}	Output Current – High			-	-24	mA
I _{OL}	Output Current – Low			_	24	mA

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- V_{IN} from 30% to 70% V_{CC}; see individual Data Sheets for devices that differ from the typical input rise and fall times.
 V_{IN} from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

DC CHARACTERISTICS

			74	AC	74AC		
Symbol	Parameter	V _{CC} (V)	T _A = -	+25°C	T _A =-40°C to +85°C	Unit	Conditions
		(*)	Тур	G	uaranteed Limits		
V _{IH}	Minimum High Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	٧	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{OH}	Minimum High Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	٧	I _{OUT} = -50 μA
		3.0 4.5 5.5	- - -	2.56 3.86 4.86	2.46 3.76 4.76	V	*V _{IN} = V _{IL} or V _{IH} -12 mA I _{OH} -24 mA -24 mA
V _{OL}	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	V	Ι _{ΟUT} = 50 μΑ
		3.0 4.5 5.5	- - -	0.36 0.36 0.36	0.44 0.44 0.44	V	*V _{IN} = V _{IL} or V _{IH} 12 mA I _{OL} 24 mA 24 mA
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	$V_I = V_{CC}$, GND
I _{OLD}	†Minimum Dynamic	5.5	-	_	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	-	-	- 75	mA	V _{OHD} = 3.85 V Min
Icc	Maximum Quiescent Supply Current	5.5	-	8.0	80	μΑ	V _{IN} = V _{CC} or GND

 $^{^\}star All$ outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

NOTE: I_{IN} and I_{CC} @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V V_{CC} .

AC CHARACTERISTICS (For Figures and Waveforms - See Section 3 of the ON Semiconductor FACT Data Book, DL138/D)

	Symbol Parameter			74AC		74.	AC		
Symbol			T _A = +25°C C _L = 50 pF			T _A = -40°C to +85°C C _L = 50 pF		Unit	Fig. No.
			Min	Тур	Max	Min	Max		
t _{PLH}	Propagation Delay D _n to Q _n	3.3 5.0	2.0 2.0	9.0 6.5	14.5 10.0	1.5 1.5	17.0 11.5	ns	3–5
t _{PHL}	Propagation Delay D _n to Q _n	3.3 5.0	2.0 2.0	9.0 6.0	13.5 9.5	1.5 1.5	16.0 11.0	ns	3–5
t _{PLH}	Propagation Delay E to Q _n	3.3 5.0	2.0 2.0	10.5 7.0	15.0 10.5	1.5 1.5	17.5 12.5	ns	3–6
t _{PHL}	Propagation Delay E to Q _n	3.3 5.0	2.0 2.0	8.0 7.5	12.5 9.0	1.5 1.5	15.0 11.0	ns	3–6
t _{PLH}	Propagation Delay Address to Q _n	3.3 5.0	2.0 2.0	12.0 8.0	19.0 13.0	1.5 1.5	22.5 15.5	ns	3–6
t _{PHL}	Propagation Delay Address to Q _n	3.3 5.0	2.0 2.0	10.0 7.0	16.0 11.0	1.5 1.5	19.0 13.0	ns	3–6
t _{PHL}	Propagation Delay MR to Q	3.3 5.0	2.0 2.0	8.0 6.0	12.0 9.0	1.5 1.5	13.5 10.0	ns	3–7

^{*}Voltage Range 3.3 V is 3.3 V ± 0.3 V. *Voltage Range 5.0 V is 5.0 V ± 0.5 V.

AC OPERATING REQUIREMENTS

				74AC	74AC		
Symbol	Parameter	V _{CC} * (V)	T _A = +25°C C _L = 50 pF		T _A = -40°C to +85°C C _L = 50 pF	Unit	Fig. No.
			Typ Guarante		teed Minimum		
t _s	Setup Time, HIGH or LOW D _n to E	3.3 5.0	- -	3.5 2.5	4.5 3.5	ns	3–9
t _h	Hold Time, HIGH or LOW D_n to \overline{E}	3.3 5.0	-	2.5 2.0	2.5 2.0	ns	3–9
t _s	Setup Time Address to E	3.3 5.0	-	7.0 4.0	9.0 6.0	ns	3–6
t _h	Hold Time Address to $\overline{\mathbb{E}}$	3.3 5.0	-	2.0 2.0	2.0 2.0	ns	3–6
t _w	Minimum Pulse Width MR	3.3 5.0	- -	6.0 5.5	6.5 6.0	ns	3–6
t _w	Minimum Pulse Width E	3.3 5.0	_ _	6.5 5.5	7.0 6.0	ns	3–6

^{*}Voltage Range 3.3 V is 3.3 V ± 0.3 V. *Voltage Range 5.0 V is 5.0 V ± 0.5 V.

DC CHARACTERISTICS

			74	CT	74ACT		
Symbol	Parameter	V _{CC} (V)	T _A = -	+25°C	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	Unit	Conditions
		(*)	Тур	G	uaranteed Limits		
V _{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V	$V_{OUT} = 0.1 \text{ V}$ or $V_{CC} - 0.1 \text{ V}$
V _{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I _{OUT} = -50 μA
		4.5 5.5	_ _	3.86 4.86	3.76 4.76	٧	*V _{IN} = V _{IL} or V _{IH} -24 mA I _{OH} -24 mA
V _{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	I _{OUT} = 50 μA
		4.5 5.5	- -	0.36 0.36	0.44 0.44	V	*V _{IN} = V _{IL} or V _{IH} 24 mA I _{OL} 24 mA
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μА	V _I = V _{CC} , GND
ΔI_{CCT}	Additional Max. I _{CC} /Input	5.5	0.6	-	1.5	mA	$V_{I} = V_{CC} - 2.1 \text{ V}$
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	-	-	- 75	mA	V _{OHD} = 3.85 V Min
I _{CC}	Maximum Quiescent Supply Current	5.5	-	8.0	80	μΑ	V _{IN} = V _{CC} or GND

 $^{^\}star\text{All}$ outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

AC CHARACTERISTICS (For Figures and Waveforms – See Section 3 of the ON Semiconductor FACT Data Book, DL138/D)

		V _{CC} * (V)		74ACT		74 <i>A</i>	CT		
Symbol	Parameter		T _A = +25°C C _L = 50 pF			T _A = -40°C C _L = 9	C to +85°C 50 pF	Unit	Fig. No.
			Min	Тур	Max	Min	Max		
t _{PLH}	Propagation Delay D _n to Q _n	5.0	2.0	6.5	11.0	1.5	12.5	ns	3–5
t _{PHL}	Propagation Delay D _n or Q _n	5.0	2.0	7.0	10.5	1.5	12.0	ns	3–5
t _{PLH}		5.0	2.0	10.5	14.0	1.5	16.5	ns	3–6
t _{PHL}	Propagation Delay E or Q _n	5.0	2.0	9.0	12.0	1.5	14.0	ns	3–6
t _{PLH}	Propagation Delay Address to Q _n	5.0	2.0	8.0	11.5	1.5	13.5	ns	3–6
t _{PHL}	Propagation Delay Address to Q _n	5.0	2.0	6.0	10.0	1.5	12.0	ns	3–6
t _{PHL}	Propagation Delay MR to Q	5.0	2.0		10.0	1.5	11.0	ns	3–7

^{*}Voltage Range 5.0 V is 5.0 V ± 0.5 V.

AC OPERATING REQUIREMENTS

				74ACT	74ACT		
Symbol	Parameter	V _{CC} * (V)	T,	_L = +25°C _L = 50 pF	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$ $C_L = 50 \text{ pF}$	Unit	Fig. No.
			Typ Guarant		nteed Minimum		
t _s	Setup Time, HIGH or LOW D _n to E	5.0	1	3.0	4.0	ns	3–9
t _h	Hold Time, HIGH or LOW D_n to \overline{E}	5.0	1	2.5	2.5	ns	3–9
t _s	Setup Time Address to $\overline{\mathbb{E}}$	5.0	1	4.5	6.5	ns	3–6
t _h	Hold Time Address to $\overline{\mathbb{E}}$	5.0	1	2.5	2.5	ns	3–6
t _w	Minimum Pulse Width MR	5.0	1	7.0	7.5	ns	3–6
t _w	Minimum Pulse Width E	5.0	ı	7.0	7.5	ns	3–6

^{*}Voltage Range 5.0 V is 5.0 V ± 0.5 V.

CAPACITANCE

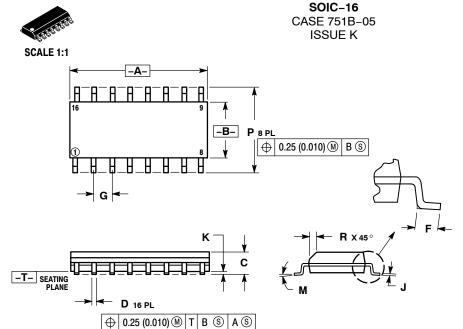
Symbol	Parameter	Value Typ	Unit	Test Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = 5.0 V
C _{PD}	Power Dissipation Capacitance	50.0	pF	V _{CC} = 5.0 V

ORDERING INFORMATION

Part Number	Package	Shipping [†]		
MC74AC259DG	SOIC-16 (Pb-Free)	48 Units / Rail		
MC74AC259DR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel		
MC74ACT259DG	SOIC-16 (Pb-Free)	48 Units / Rail		
MC74ACT259DR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27 BSC		0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR COLLECTOR BASE EMITTER NO CONNECTION	2. 3. 4. 5. 6. 7. 8. 9.	CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION ANODE CATHODE CATHODE ANODE ANODE NO CONNECTION	2. 3. 4. 5. 6. 7. 8. 9.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #2 COLLECTOR, #3	STYLE 4: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10.		н	
12.	EMITTER		CATHODE		COLLECTOR, #3				
			CATHODE			12.			
13.	BASE	13.		13.	COLLECTOR, #4	13.	BASE, #2	SOLDERING	FOOTPRINT
14. 15.	COLLECTOR EMITTER	14. 15.	NO CONNECTION ANODE	14. 15.		14.	EMITTER, #2 BASE, #1		
	COLLECTOR		CATHODE	16.	COLLECTOR, #4	15. 16.	EMITTER, #1		3X
16.	COLLECTOR	16.	CATHODE	10.	COLLECTOR, #4	10.	CIVILLICH, #1	≺ 6.	40 →
									أحدا مددن
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12
PIN 1.	DRAIN, DYE #1	PIN 1.	CATHODE	PIN 1.	SOURCE N-CH			<u> </u>	<u> </u>
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT	Γ)		_	16
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT	Γ)		*	
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH				
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT	Γ)	16)	× T	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT		0.5	ġ J 🦳	' <u> </u>
7.	DRAIN, #4	7.		7.	COMMON DRAIN (OUTPUT	Γ)	0.0	-	
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH				
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT	Γ)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT	Γ)			
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT	Γ)			
13.	GATE, #2	13.	ANODE	13.	GATE N-CH				
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT	Γ)			PITCH ↓
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT	Γ)			\ <u>+</u> _+-
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH				
								8	9 = +
									DIMENSIONS: MILLIMETERS

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